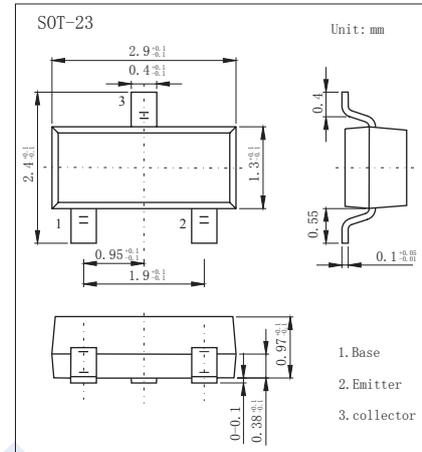


NPN Transistors

2SC2776

■ Features

- Collector Current Capability $I_c=30\text{mA}$
- Collector Emitter Voltage $V_{CE0}=20\text{V}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	30	V
Collector - Emitter Voltage	V_{CE0}	20	
Emitter - Base Voltage	V_{EB0}	4	
Collector Current - Continuous	I_c	30	mA
Collector Power Dissipation	P_c	100	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}$, $I_E = 0$	30			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1\text{mA}$, $I_B = 0$	20			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}$, $I_c = 0$	4			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 30\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 4\text{V}$, $I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 10\text{mA}$, $I_B = 1\text{mA}$			1.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 10\text{mA}$, $I_B = 1\text{mA}$			2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$	35		200	
Noise figure	NF	$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$, $f = 100\text{MHz}$, $R_g = 50\Omega$		5.5		dB
Power gain	PG	$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$, $f = 100\text{MHz}$, $R_g = 100\Omega$, $R_L = 550\Omega$, Unneutralized		17		
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		1.1		pF
Transition frequency	f_T	$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$		320		MHz

■ Classification of h_{FE}

Type	2SC2776-A	2SC2776-B	2SC2776-C
Range	35-70	60-120	100-200
Marking	VA	VB	VC